

A cross-sectional view of a semiconductor device, labeled A1. The device consists of a substrate (1) with a central region (7) and side regions (6, 9). A central layer (4) is formed on top of region (7), with a patterned layer (5) and a top layer (2) above it. A wire (3) connects the side regions (6, 9). A cross-section C1 is indicated.

FIG.2b

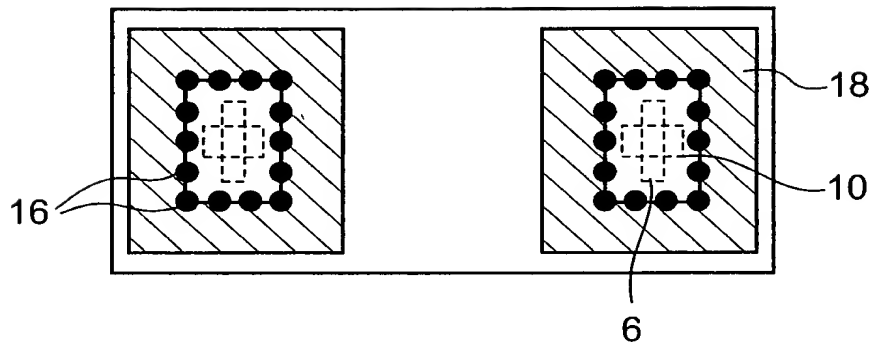


FIG.2c

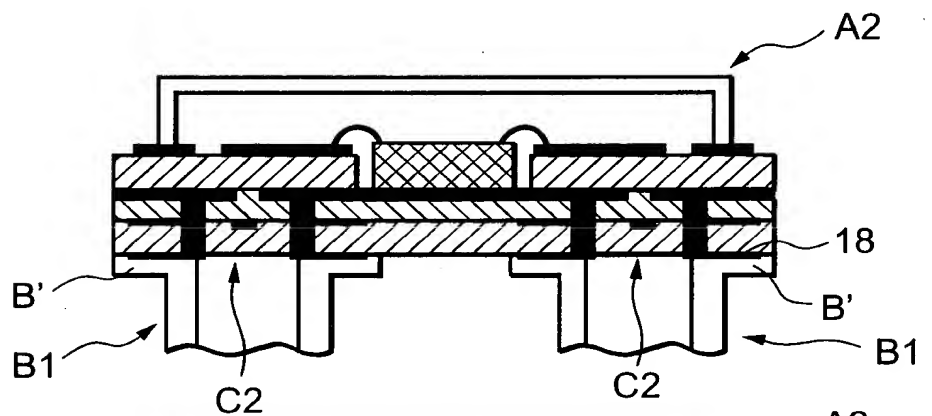
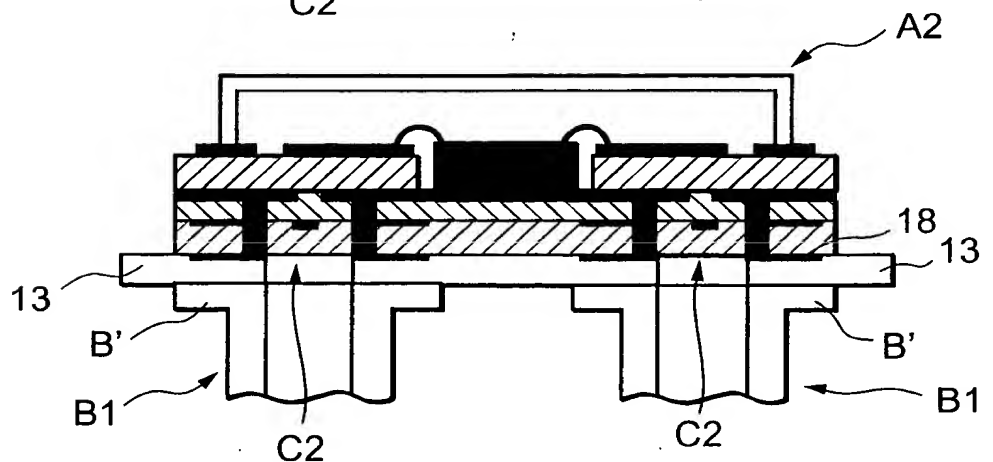
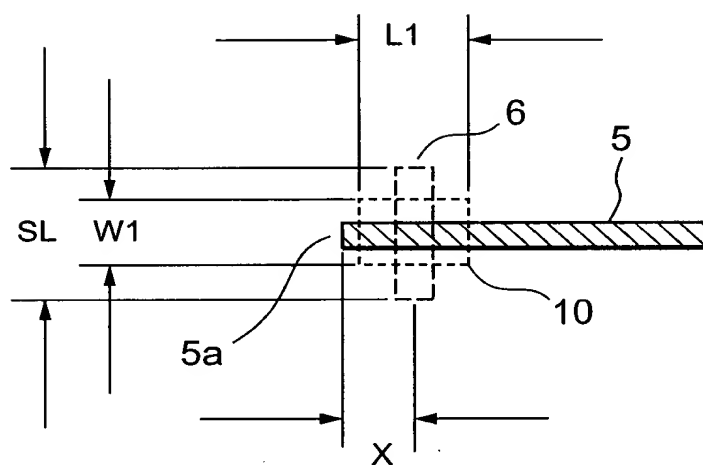


FIG. 2d



[illegible]

[illegible]

FIG.6b

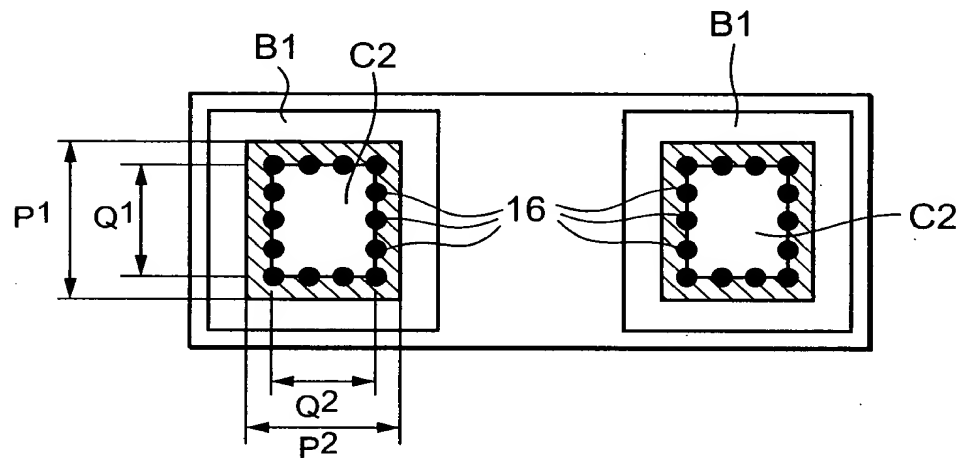


FIG.6c

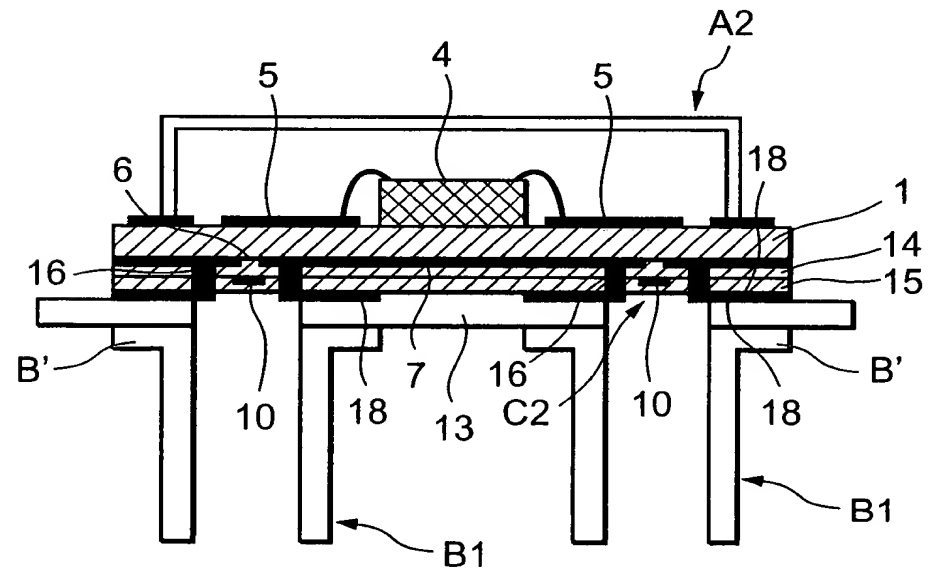


FIG.7

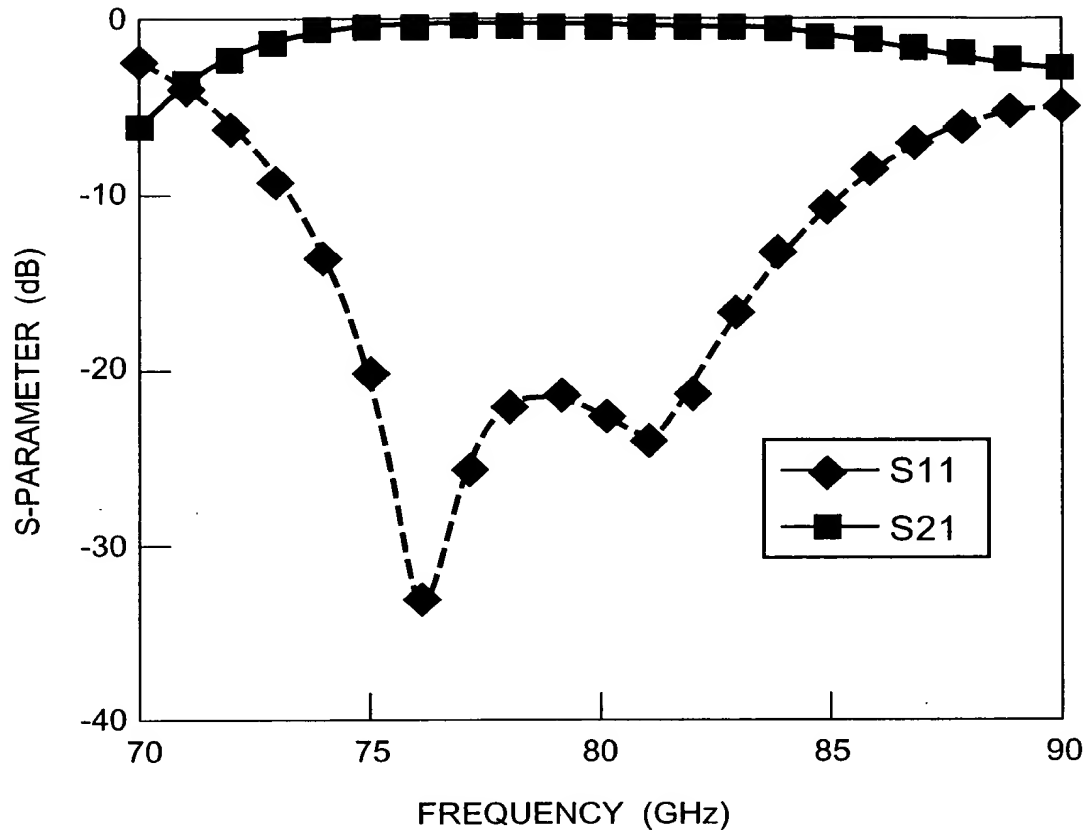


FIG.8

